- 9871191 – Magnetic random access memory with ultrathin reference layer
- 12133471 – Magnetic memory element including perpendicular enhancement layers and dual oxide cap layers
- 9401194 – Fast programming of magnetic random access memory (MRAM)
- 11348971 – Multilayered seed for perpendicular magnetic structure
- 8374025 – Spin-transfer torque magnetic random access memory (STTMRAM) with laminated free layer
- 9019758 – Spin-transfer torque magnetic random access memory with perpendicular magnetic anisotropy multilayers
- 9530479 – Method and apparatus for increasing the reliability of an access transistor coupled to a magnetic tunnel junction (MTJ)
- 10910555 – Magnetic memory element incorporating perpendicular enhancement layer
- 9444039 – Spin-transfer torque magnetic random access memory with perpendicular magnetic anisotropy multilayers
- 8917543 – Multi-state spin-torque transfer magnetic random access memory
- 12133471 – Magnetic memory element including perpendicular enhancement layers and dual oxide cap layers
- 9444038 – Magnetic random access memory with nickel/transition metal multilayered seed structure
- 9224504 – Mapping of random defects in a memory device
- 8536063 – MRAM etching processes
- 8709956 – MRAM with sidewall protection and method of fabrication
- 9520174 – Method and apparatus for writing to a magnetic tunnel junction (MTJ) by applying incrementally increasing voltage level
- 9123575 – Semiconductor memory device having increased separation between memory elements
- 9166154 – MTJ stack and bottom electrode patterning process with ion beam etching using a single mask
- 8363457 – Magnetic memory sensing circuit
- 10361362 – Magnetic random access memory with ultrathin reference layer
- 9728240 – Pulse programming techniques for voltage-controlled magnetoresistive tunnel junction (MTJ)
- 9419210 – Spin-transfer torque magnetic random access memory with perpendicular magnetic anisotropy multilayers
- 12284813 – Nonvolatile memory device including dual memory layers
- 9793003 – Programming of non-volatile memory subjected to high temperature exposure
- 8644060 – Method of sensing data of a magnetic random access memories (MRAM)
- 8975088 – MRAM etching processes
- 10050083 – Magnetic structure with multilayered seed
- 9543506 – Magnetic random-access memory with tri-layer reference layer
- 9858977 – Programming of magnetic random access memory (MRAM) by boosting gate voltage
- 9070869 – Fabrication method for high-density MRAM using thin hard mask
- 10008663 – Perpendicular magnetic fixed layer with high anisotropy

- 8942032 – Method for magnetic screening of arrays of magnetic memories
- 8611145 – Spin-transfer torque magnetic random access memory (STTMRAM) device with shared transistor and minimal written data disturbance
- 11785784 – Multilayered seed for perpendicular magnetic structure including an oxide layer
- 9318179 – Spin-transfer torque magnetic random access memory with perpendicular magnetic anisotropy multilayers
- 8971107 – Emulation of static random access memory (SRAM) by magnetic random access memory (MRAM)
- 10032979 – Magnetic memory element with iridium anti-ferromagnetic coupling layer
- 9780300 – Magnetic memory element with composite perpendicular enhancement layer
- 9349427 – Method for screening arrays of magnetic memories
- 8861260 – Multi-port magnetic random access memory (MRAM)
- 10490737 – Magnetic memory element including magnesium perpendicular enhancement layer
- 10395710 – Magnetic memory emulating dynamic random access memory (DRAM)
- 9496489 – Magnetic random access memory with multilayered seed structure
- 9911482 – Method and apparatus for adjustment of current through a magnetoresistive tunnel junction (MTJ) based on temperature fluctuations
- 9793319 – Multilayered seed structure for perpendicular MTJ memory element
- 8313960 – Magnetic tunnel junction (MTJ) formation using multiple etching processes
- 9679625 – Perpendicular magnetic tunnel junction (pMTJ) with in-plane magneto-static switching-enhancing layer
- 10950659 – Multilayered seed for perpendicular magnetic structure
- 10727400 – Magnetic random access memory with perpendicular enhancement layer
- 8547734 – Method of reading from and writing to magnetic random access memory (MRAM)
- 8535952 – Method for manufacturing non-volatile magnetic memory
- 8760914 – Magnetic memory write circuitry
- 12278195 – Shielding of packaged magnetic random access memory
- 11854591 – Magnetic memory read circuit and calibration method therefor
- 9748471 – Perpendicular magnetic memory element having magnesium oxide cap layer
- 9305626 – Method and apparatus for reading a magnetic tunnel junction using a sequence of short pulses
- 10438997 – Multilayered seed structure for magnetic memory element including a CoFeB seed layer
- 8830737 – Method and apparatus for sensing the state of a magnetic tunnel junction (MTJ)
- 11678586 – Memory system having thermally stable perpendicular magneto tunnel junction (MTJ) and a method of manufacturing same
- 10515681 – Power-efficient programming of magnetic memory
- 10347691 – Magnetic memory element with multilayered seed structure
- 9559144 – Magnetic random access memory element having tantalum perpendicular enhancement layer

- 11758822 – Magnetic memory element incorporating dual perpendicular enhancement layers
- 8891326 – Method of sensing data in magnetic random access memory with overlap of high and low resistance distributions
- 10720469 – Multilayered seed structure for magnetic memory element including a CoFeB seed layer
- 8883520 – Redeposition control in MRAM fabrication process
- 9070692 – Shields for magnetic memory chip packages
- 10818330 – Fast programming of magnetic random access memory (MRAM)
- 9419207 – Magnetic random access memory with multilayered seed structure
- 11417836 – Magnetic memory element incorporating dual perpendicular enhancement layers
- 8796795 – MRAM with sidewall protection and method of fabrication
- 10832751 – Magnetic memory and method for using the same
- 9082695 – Vialess memory structure and method of manufacturing same
- 9548448 – Memory device with increased separation between memory elements
- 11289142 – Nonvolatile memory sensing circuit including variable current source
- 9070855 – Magnetic random access memory having perpendicular enhancement layer
- 8975089 – Method for forming MTJ memory element
- 10079338 – Magnetic memory element with perpendicular enhancement layer